

/ Descriptions

WR0459I ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a TO-126F Plastic Package.

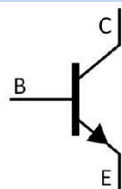
/ Features

Љ 5VE97<+D, Ы ´
Complementary pair with 2SB649(A).

/ Applications

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Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



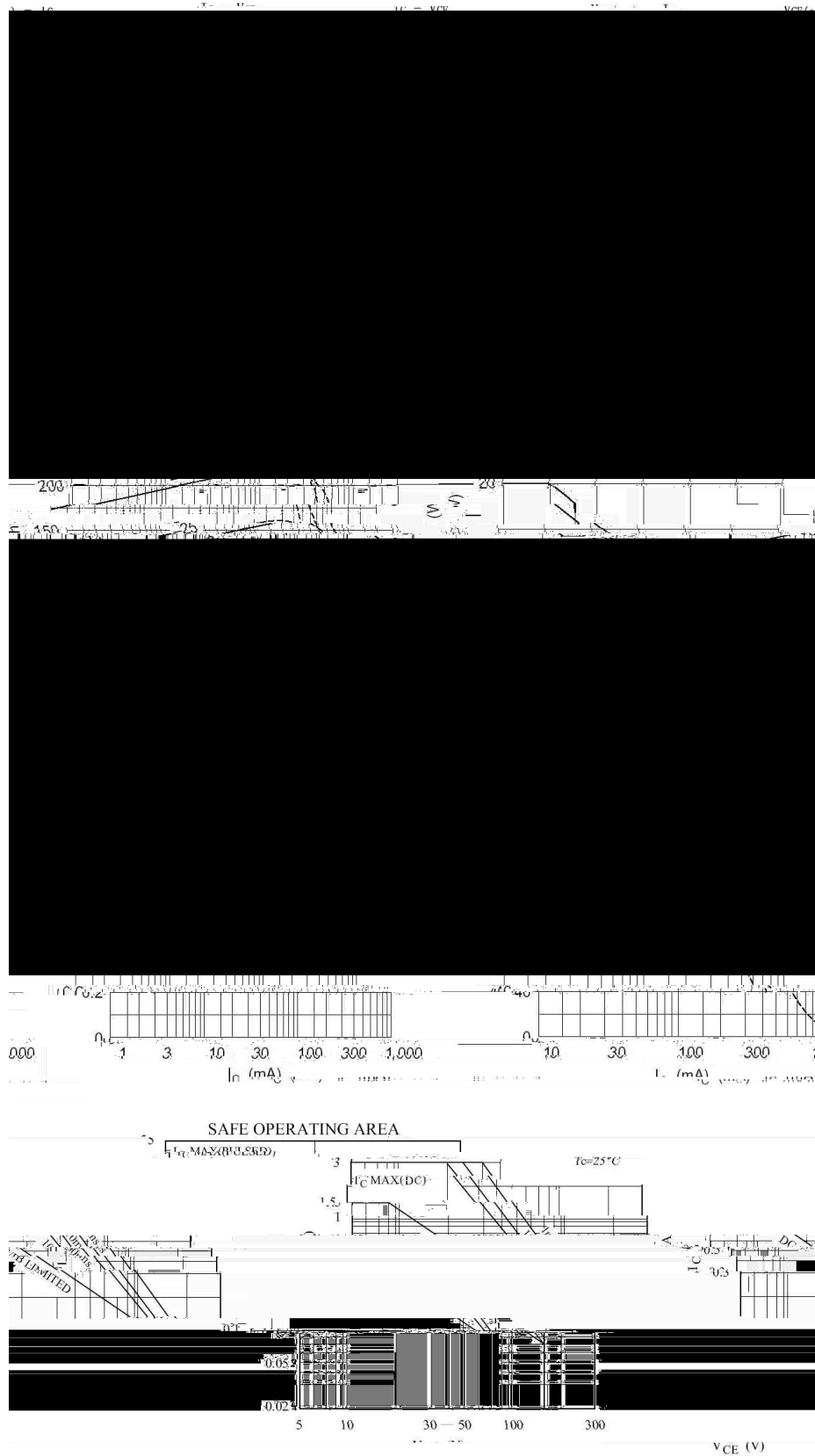
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

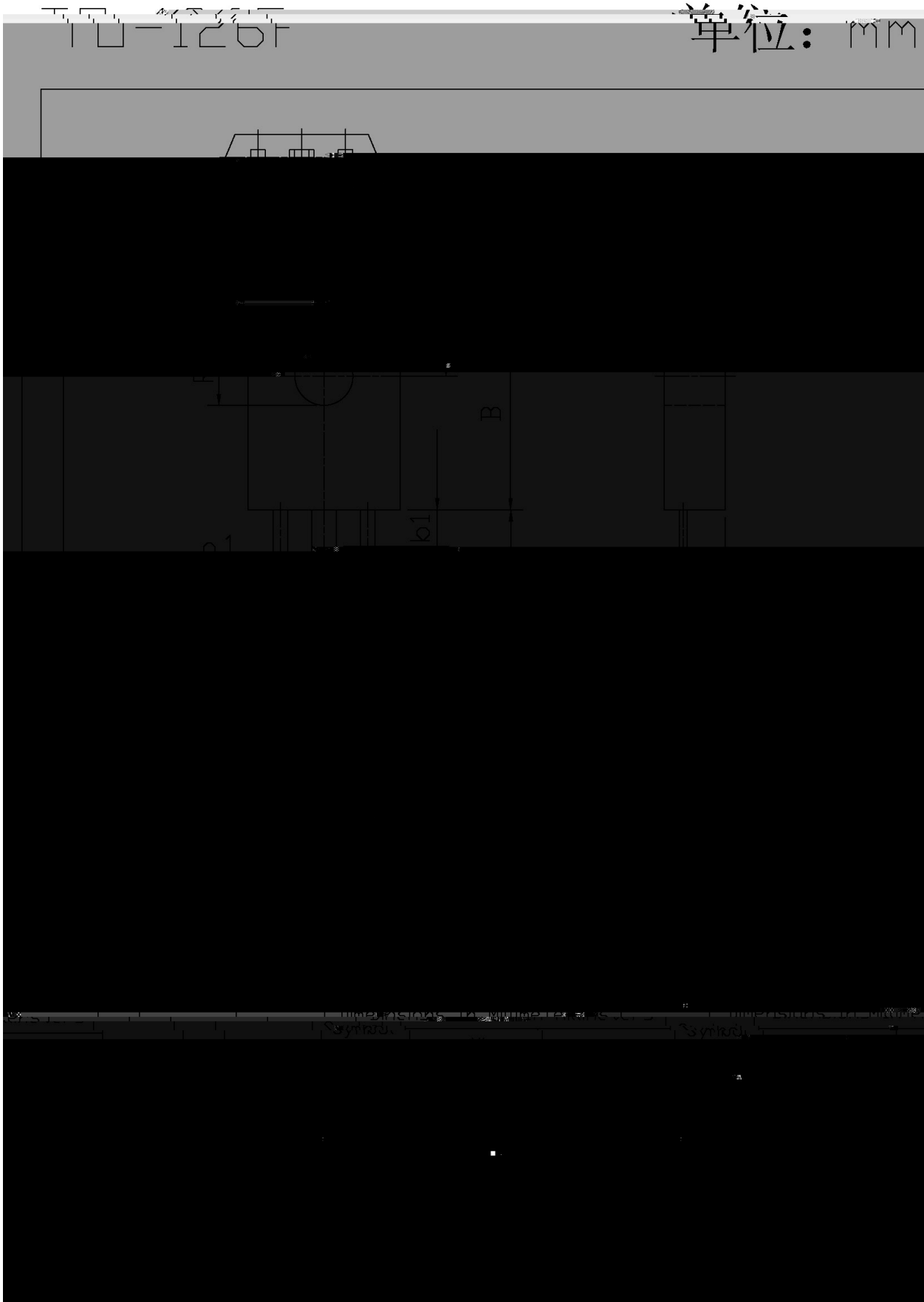
h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	60 120	100 200	160 320

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	120	V

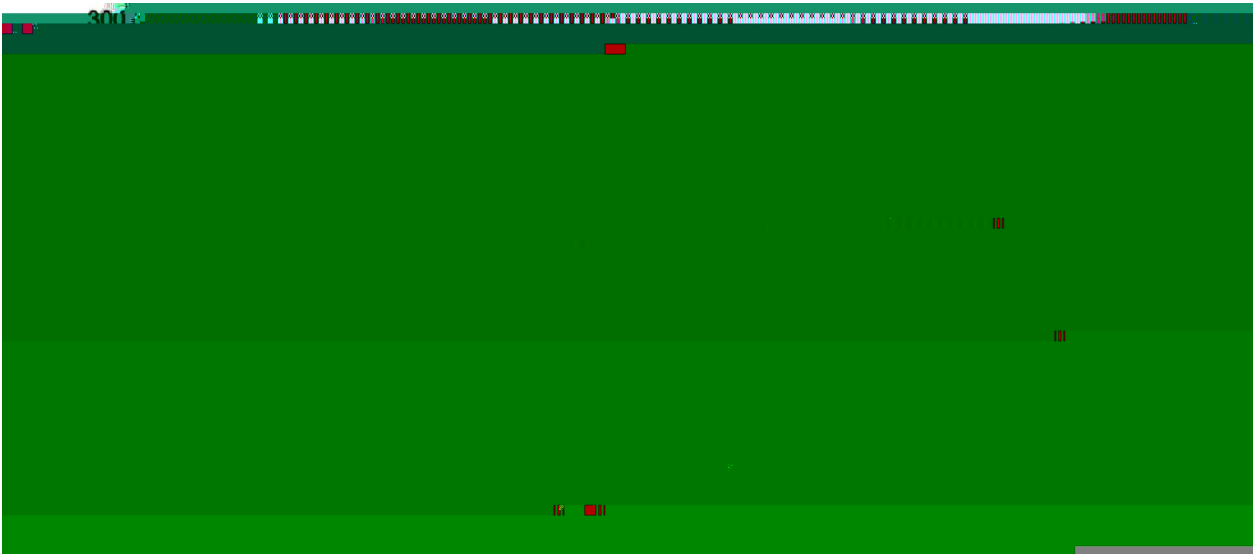
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



1. 25~150℃, Time: 60~90sec;
2. 255±5℃, Duration: 5±0.5sec;
3. Cooling Speed: 2~10℃/sec.

- Note:
- 1.Preheating:25~150℃, Time:60~90sec.
- 2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

5 • hu q t ~ 255°